

isc Silicon PNP Power Transistor

2SB995

DESCRIPTION

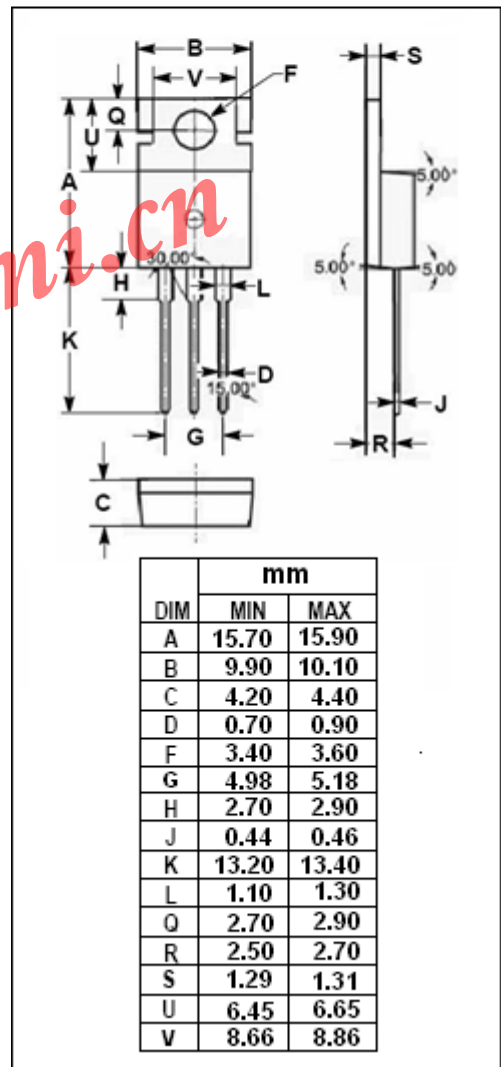
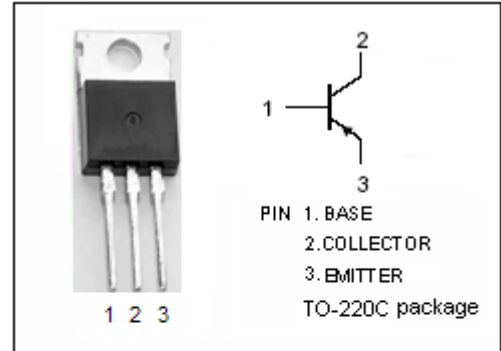
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -100V(\text{Min})$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -2.0V(\text{Max}) @ I_C = -4A$
- Complement to Type 2SD1355

APPLICATIONS

- Power amplifier applications.
- Recommended for 30W high-fidelity audio frequency amplifier output stage.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-100	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-5	A
$I_B$	Base Current-Continuous	-0.5	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



## isc Silicon PNP Power Transistor

2SB995

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = 0	-100			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.4A			-2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -4A; V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	40		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -5V	20			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1MHz		270		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V		5		MHz

◆ h<sub>FE-1</sub> Classifications

R	O	Y
40-80	70-140	120-240